

2SD965A TRANSISTOR (NPN)

FEATURES

- Audio amplifier
- Flash unit of camera
- Switching circuit



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	40	V	
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{EBO}	Emitter-Base Voltage	7	V	
Ic	Collector Current -Continuous	continuous 5		
Pc	Collector Power Dissipation	750	mW	
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~150	$^{\circ}$	

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA. I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} = 10V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
	h _{FE(1)}	V _{CE} = 2 V, I _C =1mA		200		
DC current gain	h _{FE'(2)}	$V_{CE} = 2V, I_{C} = 500mA$	230		800	
	h _{FE(3)}	V _{CE} = 2V, I _C =2A	150			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3A, I _B =0.1A			1	V
Transition frequency	f _T	V _{CE} =6V, I _C =50mA		150		MHz
Out capacitance	Cob	V_{CB} =20 V , I_E =0, f =1M H_Z			50	pF

CLASSIFICATION OF h_{FE(2)}

Rank	Q	R	s
Range	230-380	340-600	560-800



